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Yamada et al.

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(45) **Date of Patent: ** Jul. 8, 2003**

(54) **SEMICONDUCTOR DEVICE**

(75) Inventors: **Junji Yamada**, Tokyo (JP); **Seiji Saiki**, Fukuoka (JP)

(73) Assignee: **Mitsubishi Denki Kabushiki Kaisha**, Tokyo (JP)

(**) Term: **14 Years**

(21) Appl. No.: **29/164,710**

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(51) **LOC (7) Cl.** **13-03**
(52) **U.S. Cl.** **D13/182**
(58) **Field of Search** D13/110, 123, D13/125, 179, 182; 174/16.3, 52.1, 52.2, 52.4, 261; 211/4.17, 162; 361/718, 728, 747, 748, 760, 774, 784, 785, 813, 820

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Primary Examiner—Ted Shooman
Assistant Examiner—Selina Sikder
(74) *Attorney, Agent, or Firm*—Oblon, Spivak, McClelland, Maier & Neustadt, P.C.

(57) CLAIM

The ornamental design for a semiconductor device, as shown and described.

DESCRIPTION

FIG. **1** is a front, top and right side perspective view of a semiconductor device, showing our new design;
FIG. **2** is a front elevational view thereof;
FIG. **3** is a rear elevational view thereof;
FIG. **4** is a top plan view thereof;
FIG. **5** is a bottom plan view thereof;
FIG. **6** is a right side elevational view thereof; and,
FIG. **7** is a left side elevational view thereof.

1 Claim, 3 Drawing Sheets

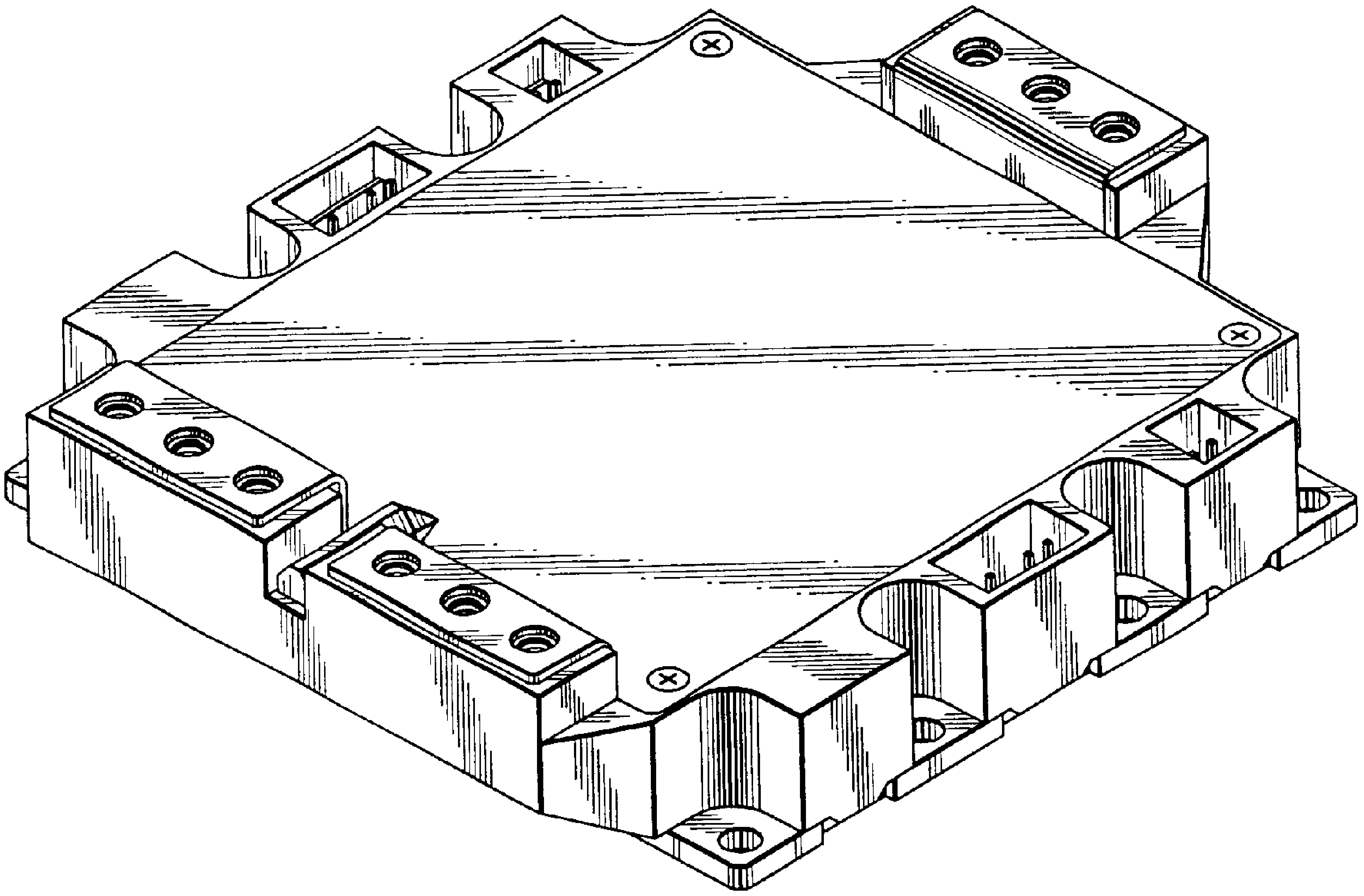

FIG.1

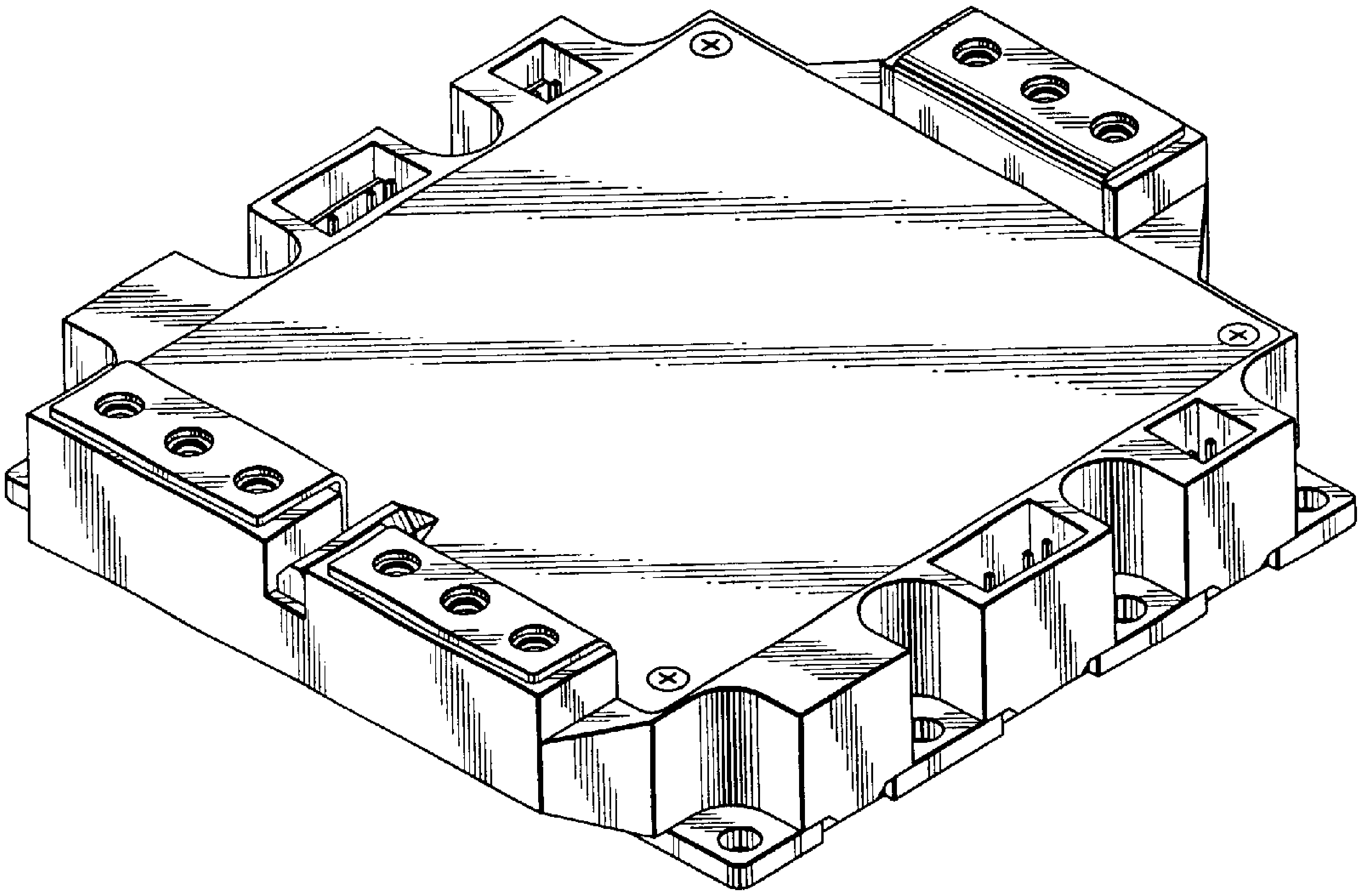

FIG.2

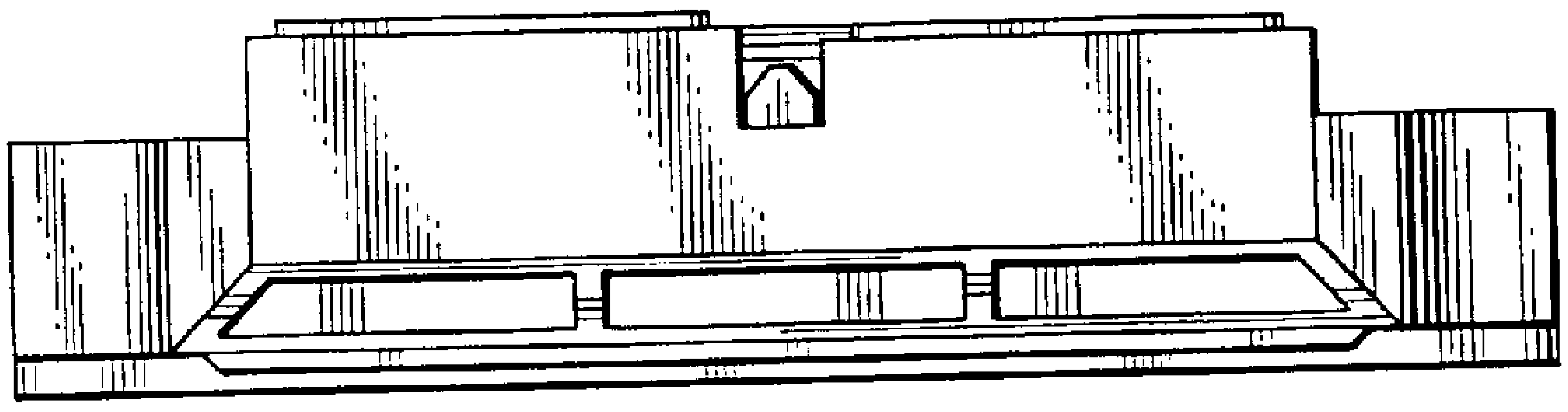

FIG.3

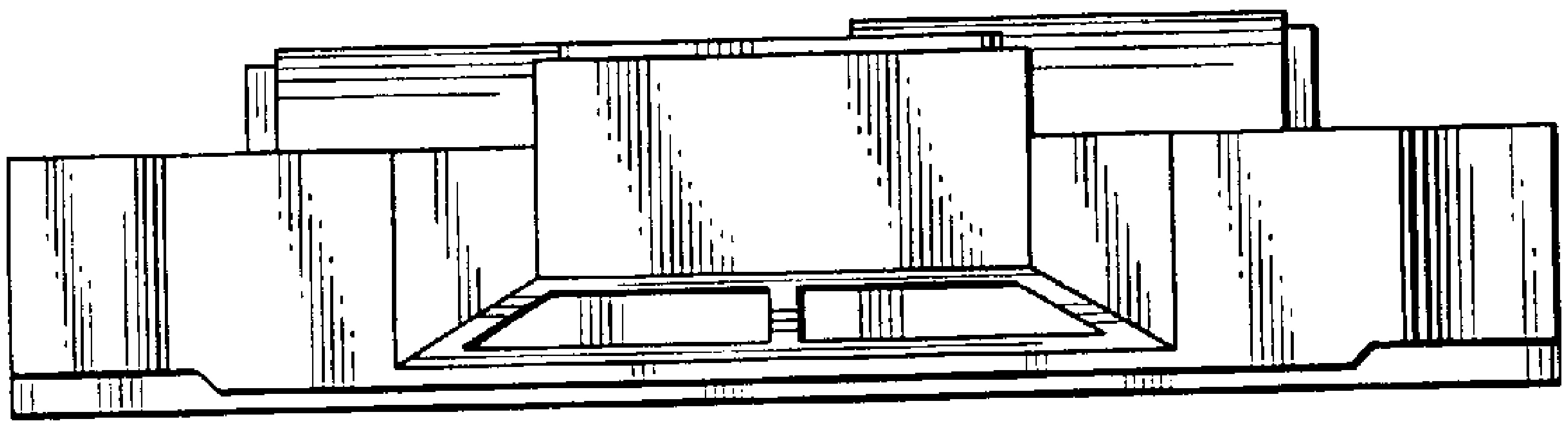

FIG.4

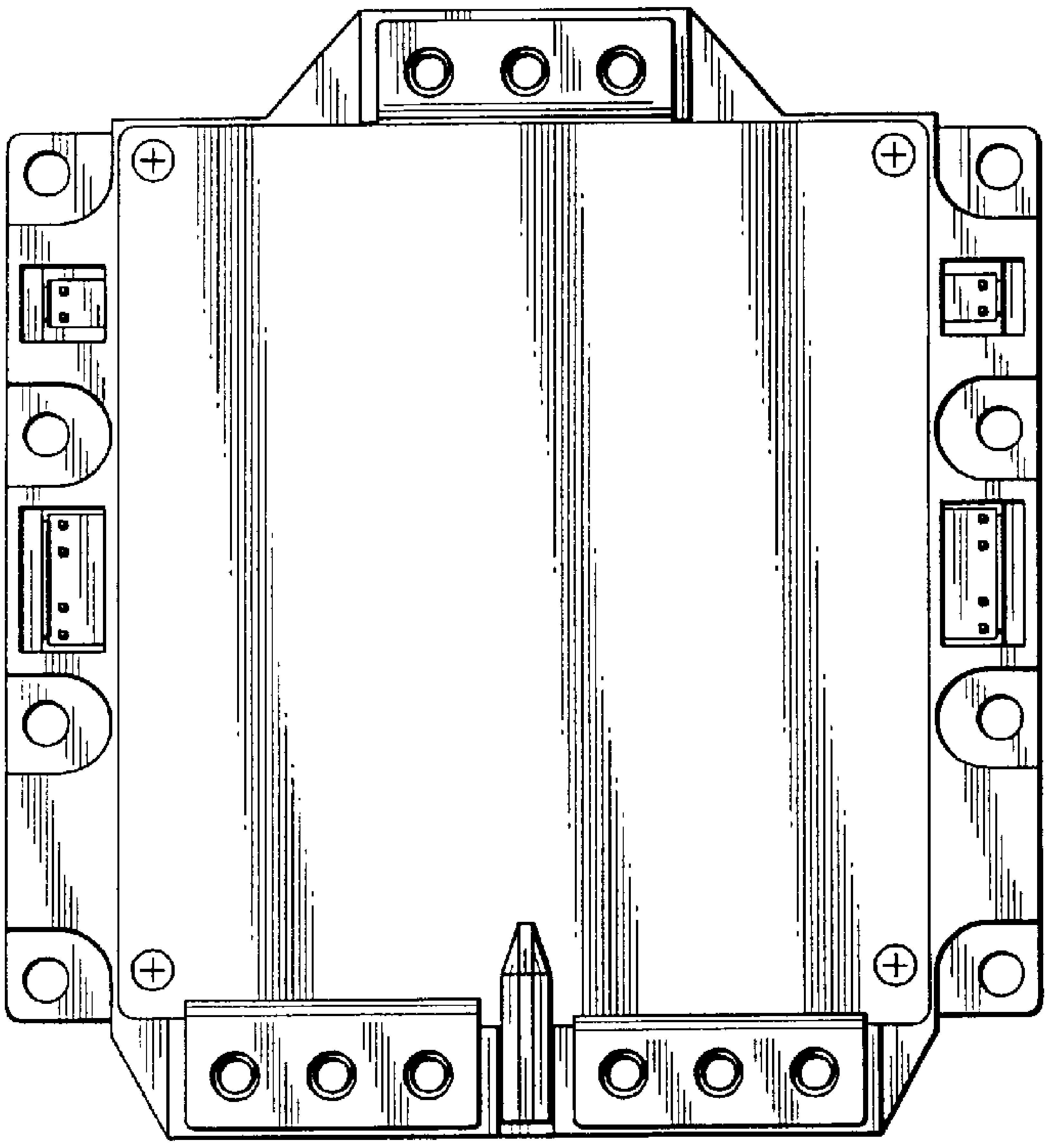

FIG.5

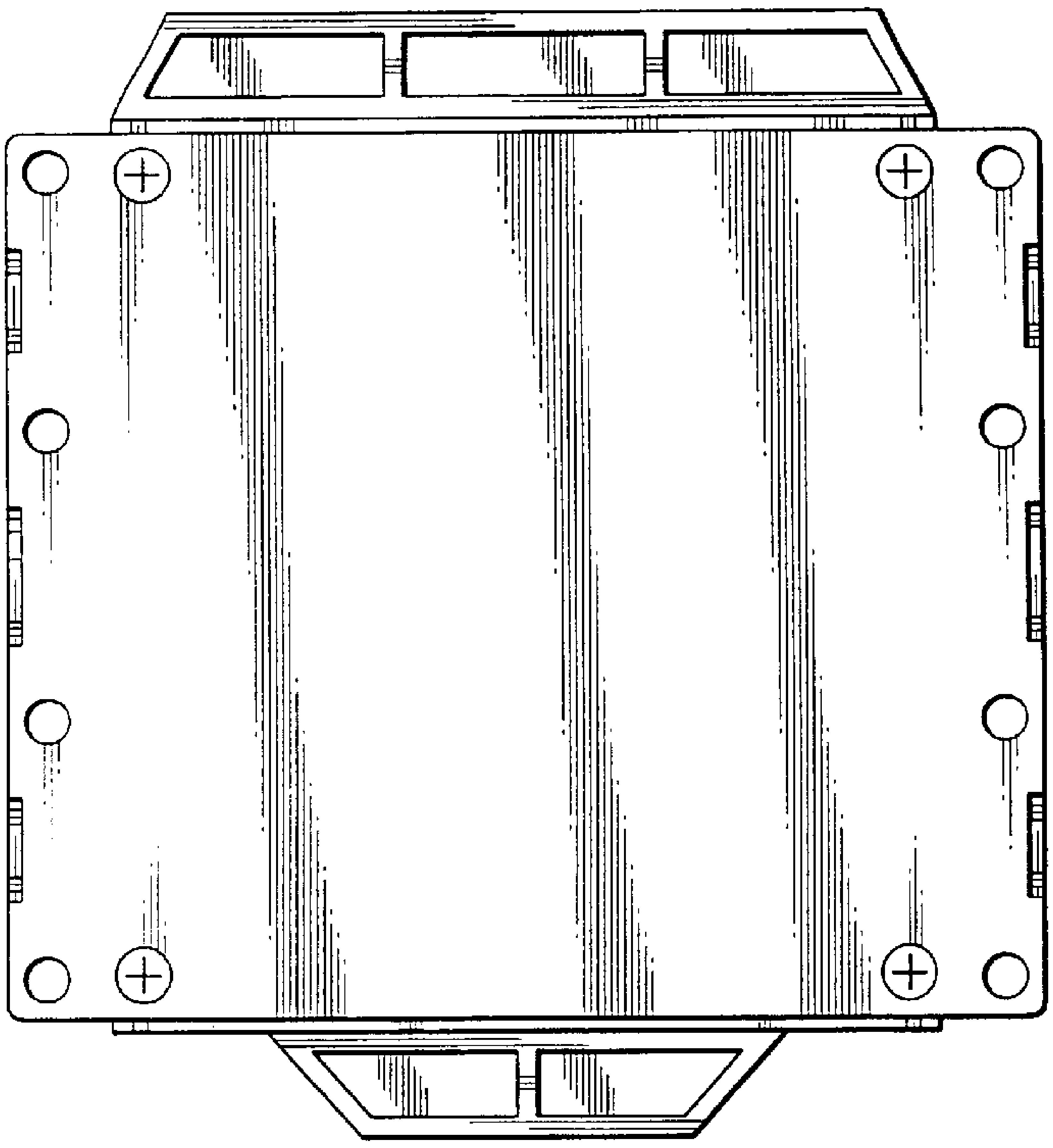

FIG.6

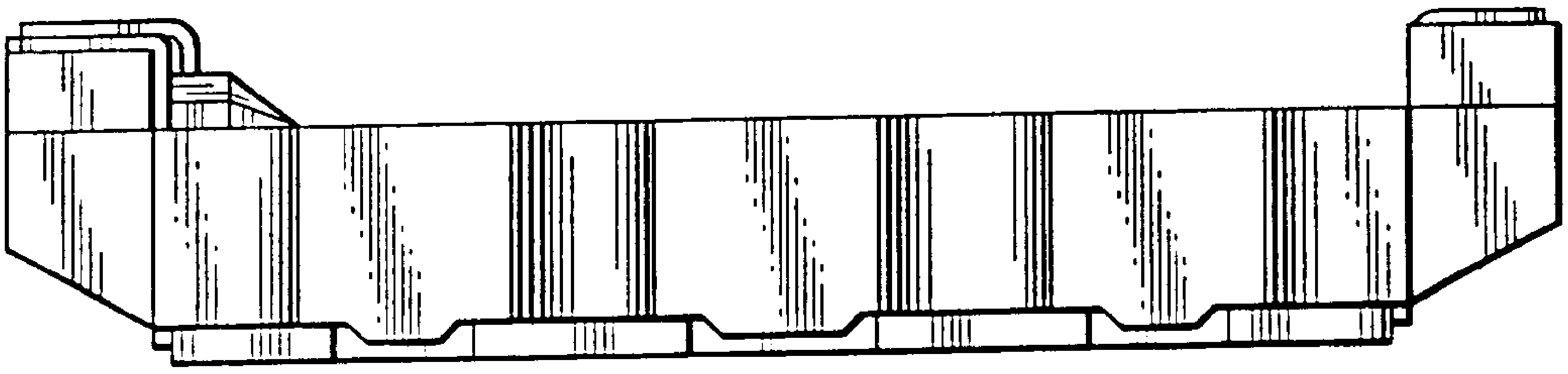

FIG.7